

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	14825	((local\$2 or selective\$2) same etch\$3) same (silicon near oxide or "SiO.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:35
L2	59	1 same (nozzle same gas\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:09
L3	57	2 and scann\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 17:43
L4	6	2 and (scann\$3 same surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 17:53
L5	20072	(flatten\$3 or planariz\$3 or smooth\$3) same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:12
L6	145	5 same 1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 17:53
L7	6	6 and (scann\$3 same surface)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:05
L8	44	6 and scann\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 17:56
L9	11	8 and @pd<"20020722"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:09

L10	2	("6360687").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 17:58
L11	100	5 and (scann\$3 same topograp\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:13
L12	7	1 same (spray\$3 same gas\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:33
L13	1419	(local\$2 same etch\$3) same (silicon near oxide or "SiO.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:44
L14	15	13 and (spray\$3 same gas\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:35
L15	2	yanagisawa-michihiko.in. and (local\$2 same etch\$3) same (silicon near oxide or "SiO.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:43
L16	1	13 and ((control\$4 or measur\$3 or detect\$3) same (nozzle near speed))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:10
L17	78	6 and @pd<"20020722"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:46
L18	55	17 and (control\$4 or measur\$3 or detect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:47
L19	3	17 and ((control\$4 or measur\$3 or detect\$3) same (nozzle or spray\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 18:58



L20	158	134/95.3.ccls. and gas\$3	US-PGPUB; USPAT	OR	OFF	2005/05/10 19:00
L21	89	20 and @pd<"20020722"	US-PGPUB; USPAT	OR	OFF	2005/05/10 19:10
L22	3	21 and ((etch\$3 or remov\$3) same (silicon near oxide))	US-PGPUB; USPAT	OR	OFF	2005/05/10 19:05
L23	292	1 and ((nozzle or spray\$3) same gas\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:09
L24	136	23 and @pd<"20020722"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:10
L25	132	24 and (control\$4 or measur\$3 or detect\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:11
L26	132	25 and @pd<"20020722"	US-PGPUB; USPAT	OR	OFF	2005/05/10 19:10
L27	132	25 and @pd<"20020722"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:12
L28	12	27 and (flatten\$3 or planariz\$3 or smooth\$3) same wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/10 19:12